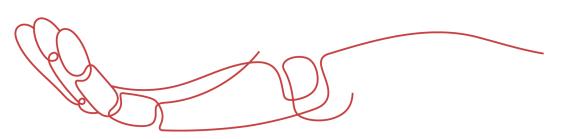




PRODUCT DATA SHEET



To learn more about JGSEMI, please visit our website at







Datasheet

Samples

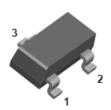
Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO_questions@jgsemi.com.



PNP Silicon Epitaxial Planar Transis

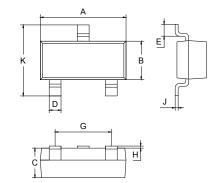
FEATURES

- High saturation voltage.
- Excellent H_{FE} Linearity.



APPLICATIONS

Switching appilication.



MAXIMUM RATING @ Ta=25 $^{\circ}$ C unless otherwise specified

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	-80	V
V _{CEO}	Collector-Emitter Voltage	-60	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-1000	mA
Pc	Collector Dissipation	500	mW
$T_{j,}T_{stg}$	Junction and Storage Temperature	-55 to +150	°C

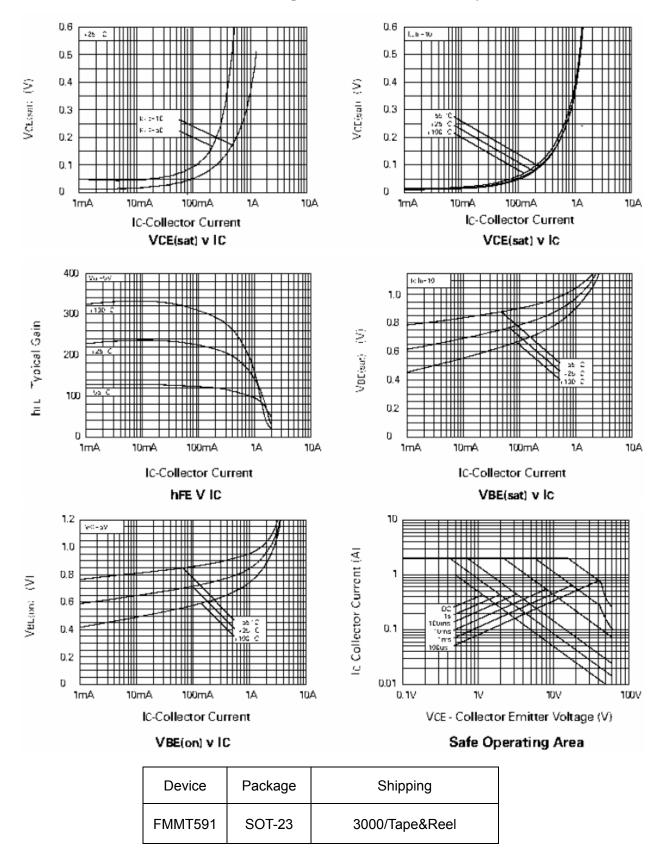
SOT-23								
Dim	Min	Max						
Α	2.70	3.10						
В	1.10	1.50						
С	1.0 Typical							
D	0.4 Typical							
E	0.35	0.48						
G	1.80	2.00						
Н	0.02	0.1						
J	0.1 Typical							
K	2.20	2.60						
All Dimensions in mm								

ELECTRICAL CHARACTERISTICS @ Ta=25 $^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA,I _E =0	-80			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-10mA,I _B =0	-60			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-100μA,I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-60V,I _E =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-4V,I _C =0			-0.1	μA
	h _{FE}	V _{CE} =-5V,I _C =-1mA	100			
DC current gain		V _{CE} =-5V,I _C =-500mA	100		300	
Do current gam		V _{CE} =-5V,I _C =-1A	80			
		V _{CE} =-5V,I _C =-2A	15			
Collector emitter esturation voltage	V _{CE(sat)}	I _C =-500mA, I _B =-50mA			-0.3	
Collector-emitter saturation voltage		I _C =-1A, I _B = -100mA			-0.6	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-1A, I _B = -100mA			-1.2	V
Base-emitter voltage	V _{BE}	V _{CE} =-5V,I _C =-1A			-1	V
Transition frequency	f _T	V _{CE} =-10V, I _C = -50mA f=100MHz	150			MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V,I _E =0,f=1MHz			10	pF



TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified





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